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# 2SC5022

Silicon NPN Triple Diffused

# HITACHI

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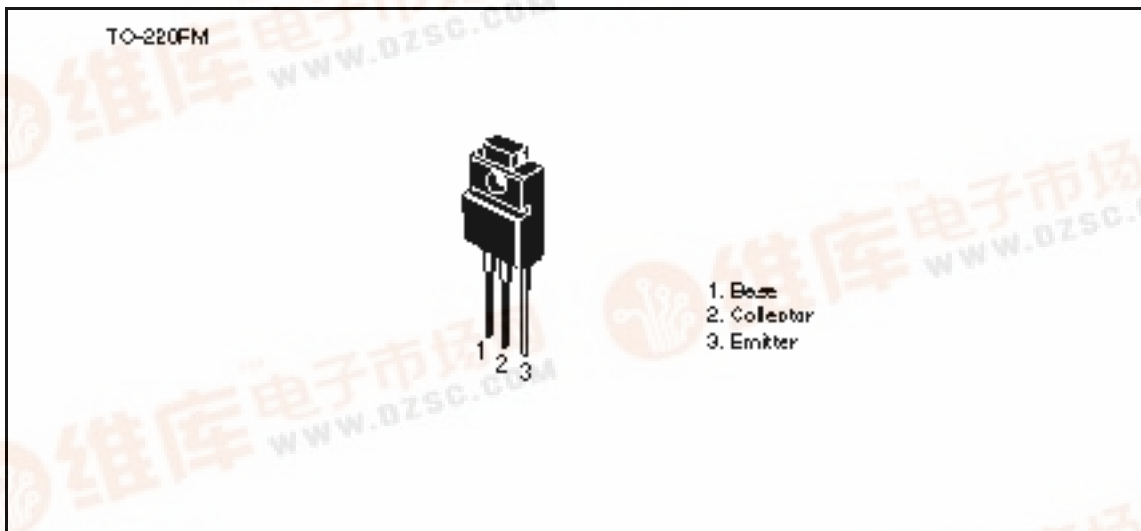
## Application

High voltage amplifier

## Features

- High breakdown voltage  $V_{(BR)CEO} = 1500 \text{ V Min}$

## Outline



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## 2SC5022

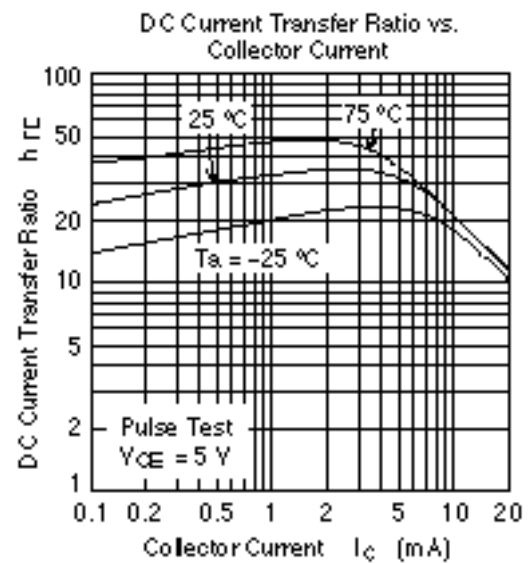
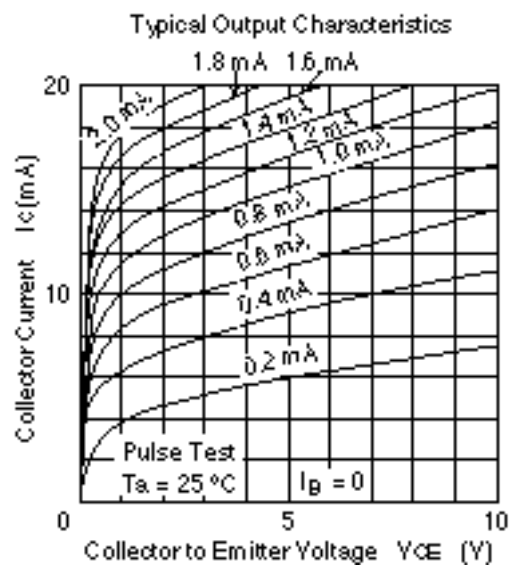
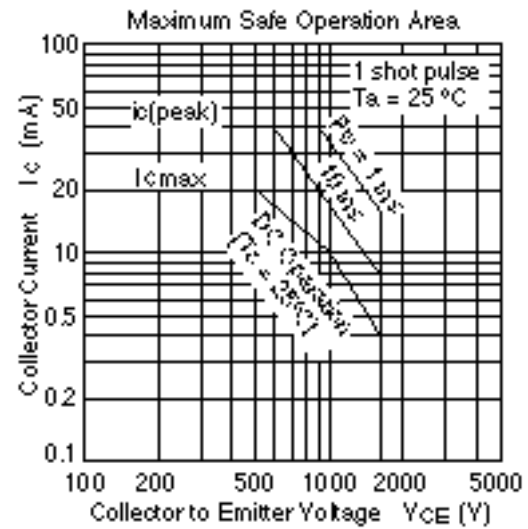
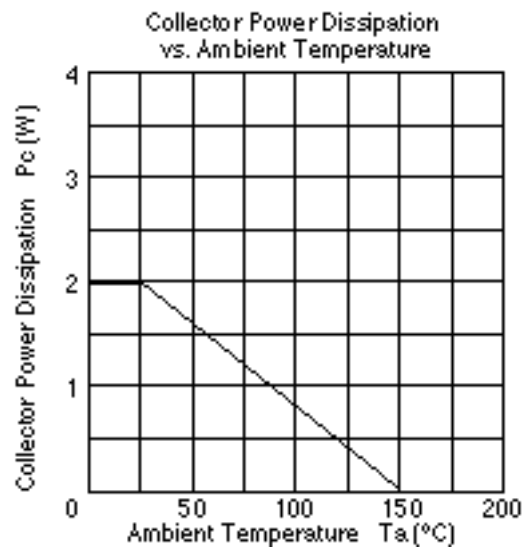
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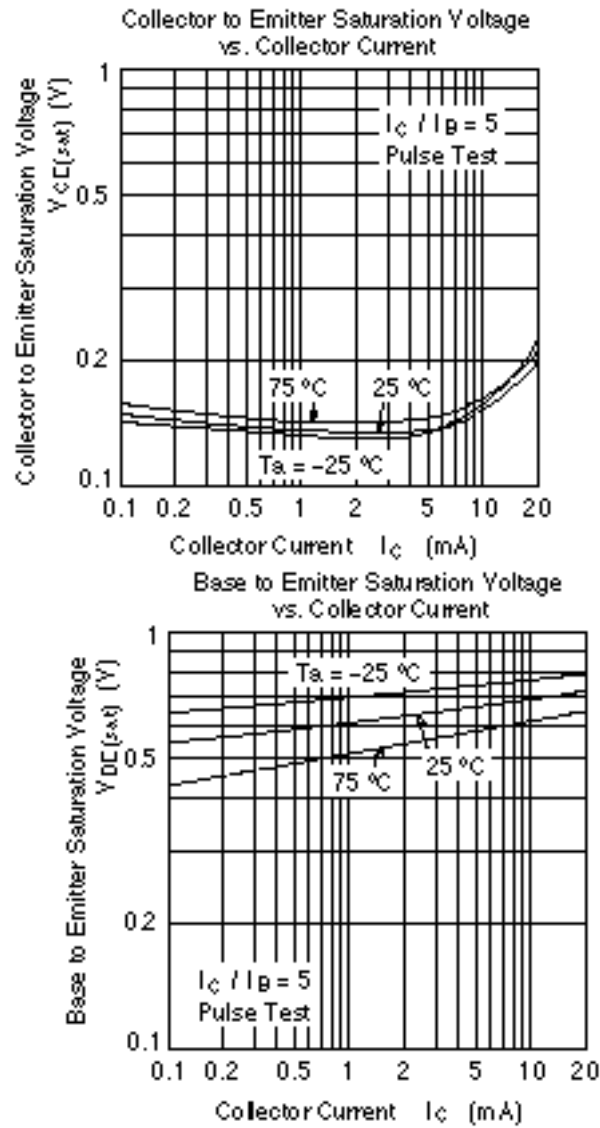
### Absolute Maximum Ratings (Ta = 25°C)

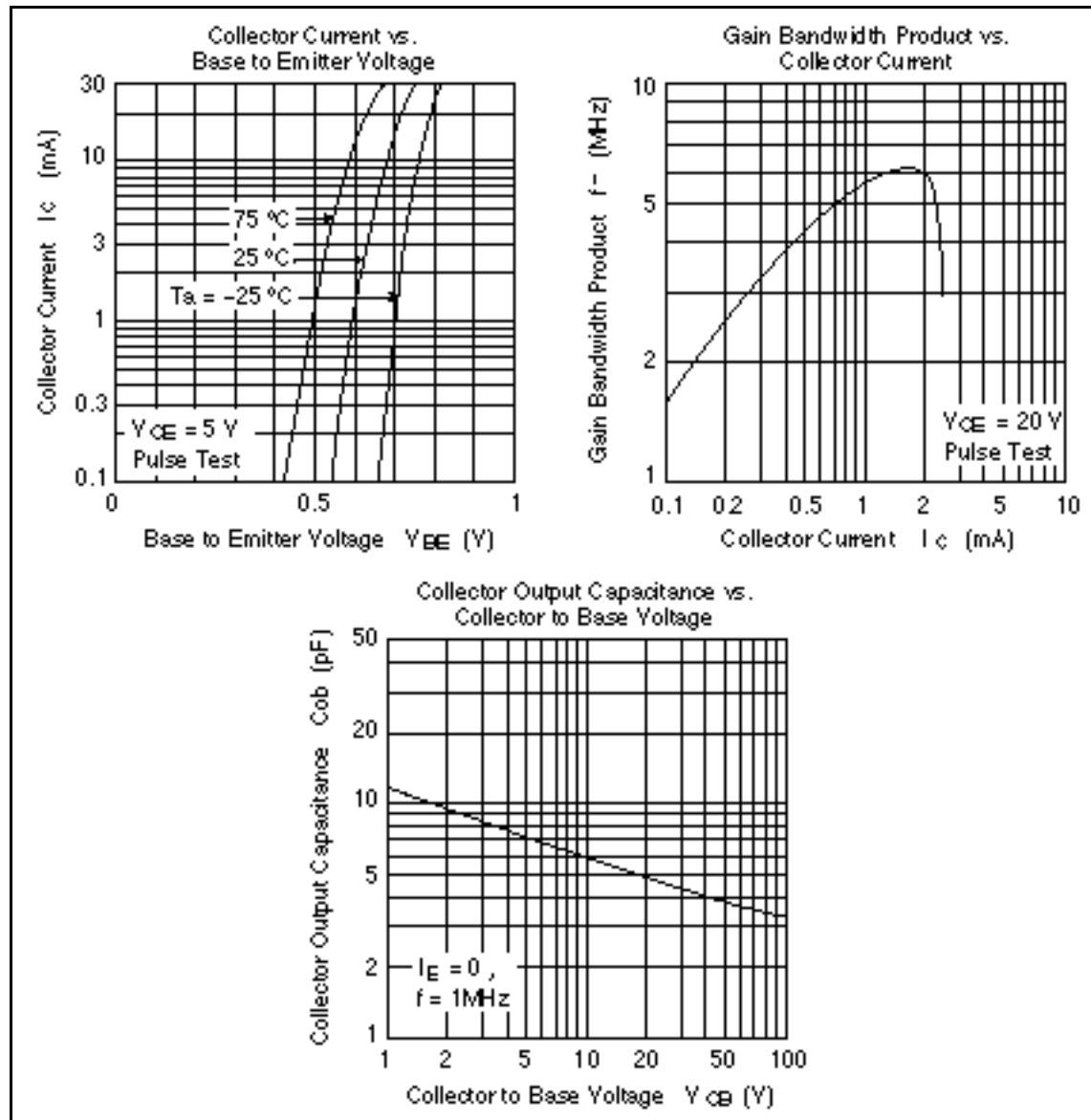
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	1500	V
Collector to emitter voltage	$V_{CEO}$	1500	V
Emitter to base voltage	$V_{EBO}$	6	V
Collector current	$I_C$	20	mA
Collector peak current	$I_{C(peak)}$	40	mA
Collector power dissipation	$P_C$	2	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	−55 to +150	°C

### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector cutoff current	$I_{CES}$	—	—	10	μA	$V_{CE} = 1500\text{ V}$ , $R_{BE} = 0$
Collector cutoff current	$I_{CEO}$	—	—	100	μA	$V_{CE} = 1500\text{ V}$ , $R_{BE} =$
Emitter cutoff current	$I_{EBO}$	—	—	10	μA	$V_{EB} = 6\text{ V}$ , $I_C = 0$
DC current transfer ratio	$h_{FE}$	10	—	—		$V_{CE} = 5\text{ V}$ , $I_C = 1\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5.0	V	$I_C = 10\text{ mA}$ , $I_B = 2\text{ mA}$







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